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Single Channel, AC/DC Sensing Input, Phototransistor Optocoupler In Half-Pitch Mini-Flat 4-Pin Package

The FODM217 series consist of a gallium arsenide infrared emitting diode driving a phototransistor. The FODM214 series consist of two gallium arsenide infrared emitting diodes connected in inverse parallel for AC operation. Both were built in a compact, half-pitch, mini-flat, 4-pin package. The lead pitch is 1.27 mm.

Features

Current Transfer Ratio Ranges from 20 to 600%

at $I_F = \pm 1$ mA, $V_{CE} = 5$ V, $T_A = 25$ °C

- FODM214 20 to 400%
- ◆ FODM214A 50 to 250%

at $I_F = 5$ mA, $V_{CE} = 5$ V, $T_A = 25$ °C

- FODM217A 80 to 160%
- ◆ FODM217B 130 to 260%
- FODM217C 200 to 400%
- FODM217D 300 to 600%
- Safety and Regulatory Approvals:
 - ◆ UL1577, 3750 VAC_{RMS} for 1 min
 - ◆ DIN EN/IEC60747-5-5, 565 V Peak Working Insulation Voltage
- Applicable to Infrared Ray Reflow, 260°C

Typical Applications

- Primarily Suited for DC-DC Converters
- For Ground Loop Isolation, Signal to Noise Isolation
- Communications Adapters, Chargers
- Consumer Appliances, Set Top Boxes
- Industrial Power Supplies, Motor Control, Programmable Logic Control



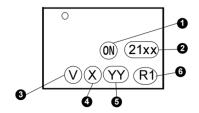
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MFP4 2.5x4.4, 1.27P CASE TBD

MARKING DIAGRAM



1. ON = Corporate Logo

2. 21xx = Device Number

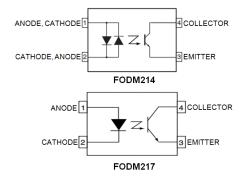
3. V = DIN EN/IEC60747–5–5 Option

4. X = One-Digit Year Code

5. YY = Digit Work Week

6. R1 = Assembly Package Code

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet

SAFETY AND INSULATIONS RATING

As per DIN EN/IEC 60747–5–5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE 0110/1.89 Table 1,	< 150 V _{RMS}	I–IV
For Rated Mains Voltage	< 300 V _{RMS}	I–III
Climatic Classification	55/110/21	
Pollution Degree (DIN VDE 0110/1.89)	2	
Comparative Tracking Index	175	

Symbol	Parameter	Value	Unit
V _{PR}	Input–to–Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	904	Vpeak
	Input–to–Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC	1060	Vpeak
V _{IORM}	Maximum Working Insulation Voltage	565	Vpeak
V _{IOTM}	Highest Allowable Over-Voltage	4,000	Vpeak
	External Creepage	≥ 5	mm
	External Clearance	≥ 5	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
T _S	Case Temperature (Note 1)	150	°C
I _{S,INPUT}	Input Current (Note 1)	200	mA
P _{S,OUTPUT}	Output Power (Note 1)	300	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V (Note 1)	> 10 ⁹	Ω

^{1.} Safety limit values – maximum values allowed in the event of a failure.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified.)

Symbol	Parameter	Value	Units
T _{STG}	Storage Temperature	−55 to +150	°C
T _{OPR}	Operating Temperature	-55 to +110	°C
T _J	Junction Temperature	-55 to +125	°C
T _{SOL}	Lead Solder Temperature (Refer to Reflow Temperature Profile)	260 for 10 sec	°C
EMITTER	•	•	
I _{F(average)}	Continuous Forward Current	50	mA
IF _(peak)	Peak Forward Current (1 μs pulse, 300 pps)	1	Α
V _R	Reverse Input Voltage	6	V
PD _{LED}	Power Dissipation (Note 2)	70	mW
DETECTOR			
I _{C(average)}	Continuous Collector Current	50	mA
V _{CEO}	Collector-Emitter Voltage	80	V
V _{ECO}	Emitter-Collector Voltage	7	V
$PD_{\mathbb{C}}$	Collector Power Dissipation (Note 2)	150	mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

^{2.} Functional operation under these conditions is not implied. Permanent damage may occur if the device is subjected to conditions outside these ratings.

ELECTRICAL CHARACTERISTICS $T_A = 25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Device	Conditions	Min.	Тур.	Max.	Units
EMITTER							
V _F	Forward Voltage	FODM214	I _F = ±20 mA		4.0	4.4	V
		FODM217	I _F = 20 mA		1.2	1.4	
I _R	Reverse Current	FODM217	V _R = 4 V			10	μΑ
C _T	Terminal Capacitance	All	V = 0 V, f = 1 kHz		30	250	pF
DETECTOR							
BV _{CEO}	Collector-Emitter Breakdown Voltage	All	$I_C = 0.1 \text{ mA}, IF = 0 \text{ mA}$	80			V
BV _{ECO}	Emitter-Collector Breakdown Voltage	All	$I_E = 10 \mu A$, $IF = 0 mA$	7			V
I _{CEO}	Collector Dark Current	All	V _{CE} = 50 V, IF = 0 mA			100	nA

TRANSFER CHARACTERISTICS T_A=25°C unless otherwise specified

Symbol	Parameter	Device	Conditions	Min.	Тур.	Max.	Units
CTR _{CE}	Current Transfer Ratio	FODM214	$I_F = \pm 1 \text{ mA}, V_{CE} = 5 \text{ V}$	20		400	%
	(collector-emitter)	FODM214A]	50		250	
		FODM217A	I _F = 5 mA, V _{CE} = 5 V	80		160	
		FODM217B		130		260	
		FODM217C		200		400	
		FODM217D		300		600	
I _C	Collector Current	FODM214	$I_F = \pm 1$ mA, $V_{CE} = 5$ V	0.2		2.5	mA
		FODM217	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	4		30	
CTR _(SAT)	Saturated Current Transfer Ratio	FODM214	$I_F = \pm 8 \text{ mA}, V_{CE} = 0.4 \text{ V}$		60		%
		FODM217	I _F = 8 mA, V _{CE} = 0.4 V		60		
I _{C(SAT)}	Collector Current	FODM214	$I_F = \pm 8 \text{ mA}, V_{CE} = 0.4 \text{ V}$		4.0		mA
		FODM217	I _F = 8 mA, V _{CE} = 0.4 V		4.8		
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	FODM214	$I_F = \pm 8 \text{ mA}, I_C = 2.4 \text{ mA}$			0.4	V
		FODM217	I _F = 8 mA, I _C = 2.4 mA			0.4	

SWITCHING CHARACTERISTICS $T_A = 25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
t _{ON}	Turn On Time	I_C = 2 mA, V_{CE} = 10 V, R_L = 100 Ω		3		μs
t _{OFF}	Turn Off Time	I_C = 2 mA, V_{CE} = 10 V, R_L = 100 Ω		3		μs
t _R	Output Rise Time (10%-90%)	I_C = 2 mA, V_{CE} = 10 V, R_L = 100 Ω		3		μs
t _F	Output Fall Time (90%-10%)	IC = 2 mA, V_{CE} = 10 V, R_L = 100 Ω		3		μs

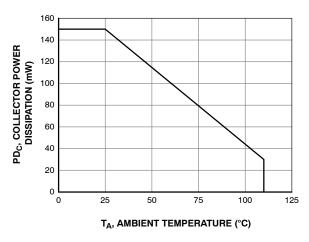
ISOLATION CHARACTERISTICS

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _{ISO}	Input-Output Isolation Voltage	Freq = 60 Hz, t = 1.0 min, $I_{I-O} \le 10 \mu A \text{ (Note 3, 4)}$	3,750			VAC _{RMS}
R _{ISO}	Isolation Resistance	V _{I-O} = 500 V (Note 3)	5 x 10 ¹⁰			Ω
C _{ISO}	Isolation Capacitance	Frequency = 1 MHz		0.6	1.0	pF

^{3.} Device is considered a two terminal device: Pin 1 and 2 are shorted together and Pins 3 and 4 are shorted together.

^{4. 3,750} VAC $_{\mbox{\scriptsize RMS}}$ for 1 minute duration is equivalent to 4,500 VAC $_{\mbox{\scriptsize RMS}}$ for 1 second duration.

TYPICAL CHARACTERISTICS



(38)

80

60

40

20

25

50

75

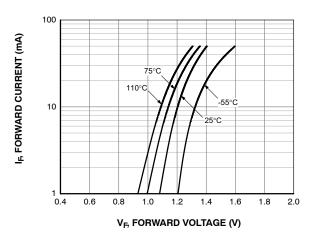
100

125

T_A, AMBIENT TEMPERATURE (°C)

Figure 1. Collector Power Dissipation vs. Ambient Temperature

Figure 2. LED Power Dissipation vs. Ambient Temperature



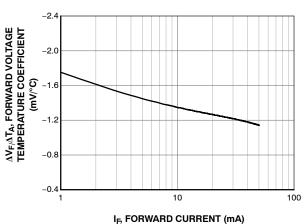
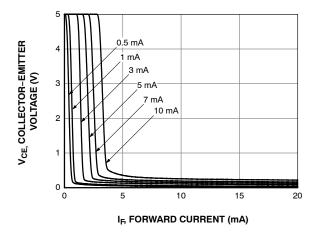


Figure 3. Forward Current vs. Forward Voltage

Figure 4. Forward Voltage Temperature Coefficient vs. Forward Current



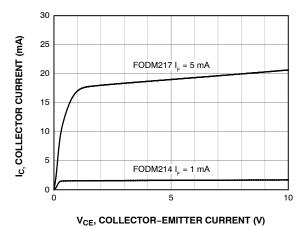
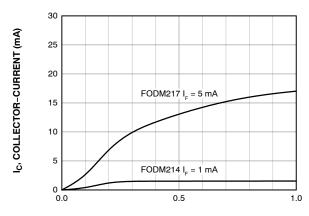


Figure 5. Collector Emitter Voltage vs. Forward Current

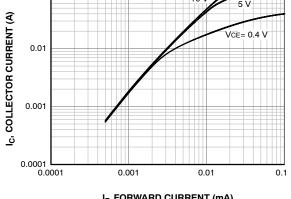
Figure 6. Collector Current vs. Collector-Emitter Voltage

0.1



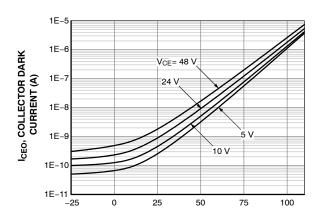
V_{CE}, COLLECTOR-EMITTER VOLTAGE (V)

Figure 7. Collector Current vs. Small Collector-Emitter Voltage

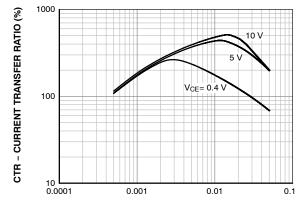


IF, FORWARD CURRENT (mA)

Figure 8. Collector Current vs. **Forward Current**



T_A, AMBIENT TEMPERATURE (°C)



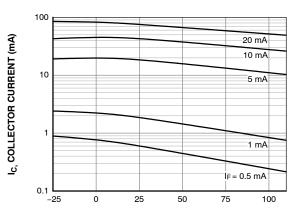
IF FORWARD CURRENT (A)

Figure 9. Collector Dark Current vs. **Ambient Temperature**

0.18 V_{CE(SAT)}, COLLECTOR-EMITTER SATURATION VOLTAGE (V) 0.14 IF = 8 mA0.10 $I_C = 2.4 \text{ mA}$ 0.08 $I_F = 1 \text{ mA}$ 0.06 Ic = 0.2 mA 0.04 IF = 20 mA Iç = 1 mA 0.02 0.00 -25 100 T_A, AMBIENT TEMPERATURE (°C)

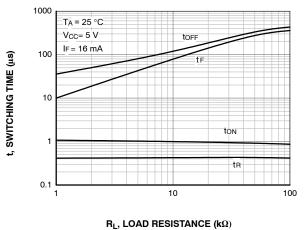
Figure 11. Collector-Emitter Saturation vs. **Ambient Temperature**

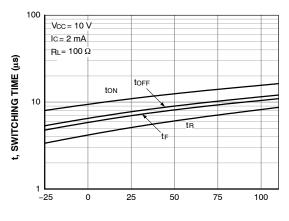
Figure 10. Current Transfer Ratio vs. **Forward Current**



TA, AMBIENT TEMPERATURE (°C)

Figure 12. Collector Current vs. **Ambient Temperature**





T_A, AMBIENT REMPERATURE (°C)

Figure 13. Switching Time vs. Load Resistance

Figure 14. Switching Time vs. Ambient **Temperature**

TEST CIRCUIT

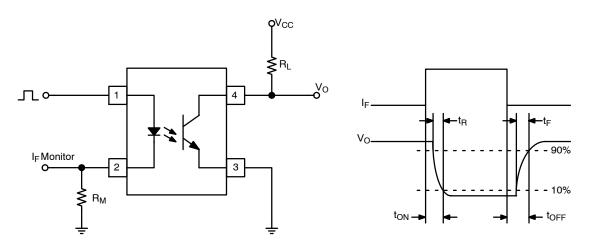


Figure 15. Test Circuit for Switching Time

REFLOW PROFILE

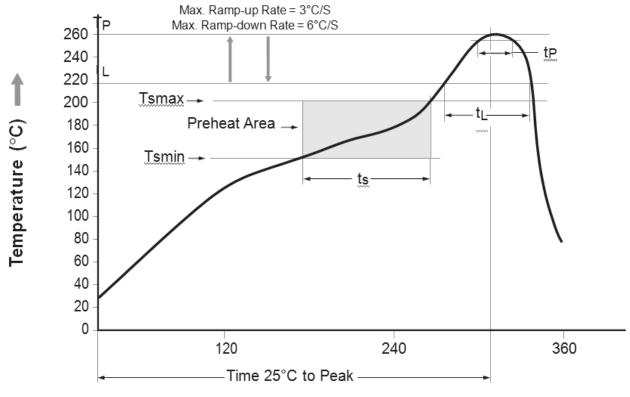


Figure 16. Reflow Profile

Profile Freature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t _S) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60–150 seconds
Peak Body Package Temperature	260°C +0°C / –5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

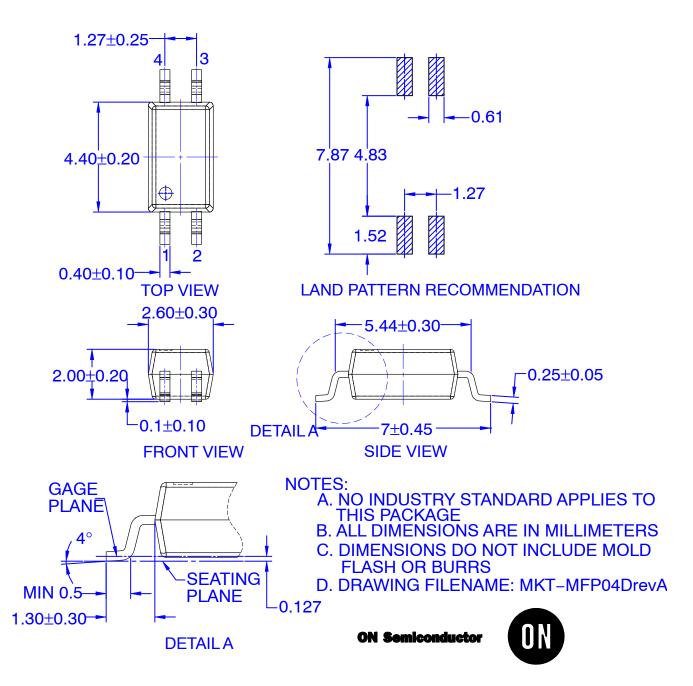
ORDERING INFORMATION (Note 5)

Part Number	Package	Packing Method
FODM214A	SOP 4-Pin	Tube (100 units)
FODM214AR2	SOP 4-Pin	Tape and Reel (3000 units)
FODM214AV	SOP 4-Pin, DIN EN/IEC60747-5-5 Option	Tube (100 units)
FODM214AR2V	SOP 4-Pin, DIN EN/IEC60747-5-5 Option	Tape and Reel (3000 units)

^{5.} The product orderable part number system listed in this table also applies to the FODM214, FODM217A, FODM217B, FODM217C, and FODM217D products.

PACKAGE DIMENSIONS

MFP4 2.5x4.4, 1.27P CASE TBD ISSUE TBD



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